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View Online at https://aerobasegroup.com/nsn/5961-01-375-1418

Inclosure Material:

Metal

Overall Length:

Between 0.330 inches and 0.505 inches

Mounting Facility Quantity:

1

Internal Configuration:

Junction contact

Mounting Method:

Threaded stud

Features Provided:

Electrostatic sensitive and hermetically sealed case

Overall Width Across Flats:

Between 0.544 inches and 0.562 inches

Thread Size:

0.250 inches

Criticality Code Justification:

Feat

Semiconductor Material:

Silicon

Voltage Rating In Volts Per Characteristic:

2.0 forward voltage, peak and 3.0 gate trigger voltage, dc

Current Rating Per Characteristic:

16.00 amperes average on-state current, 180 degrees conduction angle, average over a full 60-hz cycle

Maximum Operating Tempurature Per Measurement Point:

125.0 degrees celsius ambient air

Special Features:

Hci & esd; junction pattern arrangement: pnpn

Nuclear Hardness Critical Feature:

Hardened

Special Test Features:

Selected and tested for application in radiation hardness critical systems

Thread Series Designator:

Unf

Terminal Type And Quantity:

28 tab, solder lug and 1 threaded stud

Specification Data:

81349-mil-s-19500/108 government specification

Shelf Life:

N/a

Unit Of Measure:

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Demilitarization:

No

Fiig:

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